

204612US-2

#12/B

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
YUUCHI HIRANO ET AL. : EXAMINER: TRAN, T.
SERIAL NO: 09/802,886 :
FILED: MARCH 12, 2001 : GROUP ART UNIT: 2811
FOR: SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING
THE SAME

1 (X)
2/4/03
J. Smith
enter
3/5/03
RECEIVED
JAN 22 2003
TECHNOLOGY CENTER 2800

RESPONSE

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action of November 8, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend independent Claim 1 to read as follows:¹

SUB
C1
B1

1. (Twice Amended) A semiconductor device comprising:
an SOI substrate having a structure in which a semiconductor substrate, an insulating layer and a semiconductor layer are layered in this order;
a partial-isolation insulating film formed in a main surface of said semiconductor layer;

¹A marked-up copy of the amendments is attached hereto.